



PRESIDENCY UNIVERSITY

BENGALURU

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End - Term Examinations – May / June 2026

Date: 25-05-2026

Time: 01:00pm – 04:00pm

School: SOCSE and Allied Courses	Program: B. Tech	
Course Code: PHY3002	Course Name: MICROELECTROMECHANICAL SYSTEMS	
Semester: VI	Max Marks: 100	Weightage: 50%

CO - Levels	C01	C02	C03	C04	C05
Marks	24	14	14	24	24

Instructions:

- Read all questions carefully and answer accordingly.
- Do not write anything on the question paper other than roll number.

Part A

Answer ALL the Questions. Each question carries 2marks.

10Q x 2M=20M

1.	What does MEMS stand for? Give one example of a MEMS device found in a smartphone.	2 Marks	L1	C01
2.	What is the difference between micro-scale and macro-scale behavior? Give one example.	2 Marks	L2	C01
3.	What is Young's modulus? How does it relate to the stiffness of a MEMS beam?	2 Marks	L1	C02
4.	What is a membrane in MEMS? State one application of a MEMS membrane.	2 Marks	L1	C02
5.	What is anisotropic etching? How is it different from isotropic etching?	2 Marks	L2	C03
6.	What is the role of a sacrificial layer in surface micromachining?	2 Marks	L2	C03
7.	What is an accelerometer? How is it different from a gyroscope?	2 Marks	L1	C04
8.	What is piezoelectricity? Name two materials that show this property.	2 Marks	L1	C04
9.	What is the pull-in effect in an electrostatic actuator? Why is it important?	2 Marks	L2	C05

10.	What is a MEMS micro-mirror? Name one application.	2 Marks	L1	C05
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Part B

Answer the Questions.

Total Marks 80M

11.	a.	What are MEMS? Explain how MEMS are fabricated using IC-like batch processing. Describe how miniaturization has enabled the development of small, efficient sensors and actuators.	10 Marks	L3	C01
	b.	Explain the benefits of scaling in MEMS. How do speed, power consumption, and robustness improve when device dimensions are reduced?	5 Marks	L3	C01
	c.	How does heat conduction scale in MEMS? What happens to the thermal time constant as device size decreases? Explain with the concept of thermal scaling.	5 Marks	L3	C01

Or

12.	a.	Explain the structure and characteristics of single crystal silicon. What are Miller indices? Describe the properties of the (100), (110), and (111) crystal planes of silicon.	10 Marks	L3	C01
	b.	Explain the mechanical behavior of MEMS membranes. How does the stiffness of a membrane depend on its thickness and tension? Describe one sensing application.	5 Marks	L3	C01
	c.	Explain the guided-guided beam structure in MEMS. How is it different from a cantilever? Where is it used and why?	5 Marks	L3	C01

13.	a.	Explain the working of metal evaporation, metal sputtering, and chemical vapor deposition (CVD) for thin film deposition in MEMS. Include neat diagrams and compare the three processes.	10 Marks	L3	C02
	b.	Explain bulk micromachining in MEMS. What are the important techniques used? How are membranes, trenches, and moving structures created?	5 Marks	L3	C03
	c.	List the two types of photoresists used in MEMS fabrication and explain in detail the process of photoresists formation, photoresists development and its removal with proper diagrams.	5 Marks	L3	C03

Or

14.	a.	Explain the photoresist formation process in MEMS fabrication. Describe spin coating, soft baking, UV exposure, development, and post-baking steps with their purpose.	10 Marks	L3	C02
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	b.	Explain hermetic and non-hermetic packaging in MEMS. What materials are used in each? What types of MEMS devices require hermetic packaging?	5 Marks	L3	C03
	c.	Explain KOH anisotropic etching of silicon. Why does it etch the (100) plane faster than the (111) plane? What shapes can be created?	5 Marks	L3	C03

15.	a.	Explain the working of a MEMS pressure sensor using piezoresistive sensing. Include the Wheatstone bridge circuit, placement of resistors, and how pressure causes resistance change.	10 Marks	L3	C04
	b.	Explain capacitive sensing in MEMS. How does the capacitance change when a dielectric material is inserted or removed between the plates? Give the relevant equation.	5 Marks	L3	C04
	c.	Explain the terms sensitivity, noise, and measurement range for a MEMS sensor. Why is a high signal-to-noise ratio important in sensor design?	5 Marks	L3	C04

Or

16.	a.	Explain how a MEMS accelerometer works using capacitive sensing. Describe the proof mass, spring suspension, and how acceleration changes the capacitance gap. Include equations.	10 Marks	L3	C04
	b.	A capacitive MEMS sensor has an initial capacitance of 2 pF with a gap of 5 μm . If the gap reduces to 3 μm due to applied pressure, calculate the new capacitance. (Assume parallel plate model, $C = \epsilon A/d$)	5 Marks	L3	C04
	c.	Explain a metal strain gauge. How does it work and how is it used in MEMS pressure sensing?	5 Marks	L3	C04

17.	a.	Explain thermal actuation in MEMS. Describe the working of a U-shaped hot-arm and cold-arm thermal actuator. How does asymmetry in heating cause lateral deflection?	10 Marks	L3	C05
	b.	Explain the Seebeck effect and how it is used in a MEMS thermocouple. What are the three main effects that influence the Seebeck coefficient in silicon?	5 Marks	L3	C05
	c.	Describe four main actuation mechanisms in MEMS: electrostatic, thermal, piezoelectric, and magnetic. Compare their power consumption and displacement range in brief.	5 Marks	L3	C05

Or

18.	a.	Explain the working of a comb-drive electrostatic actuator in MEMS. How are the electrostatic forces generated? Describe the equation for force and how it is used to produce linear motion.	10 Marks	L3	C05
	b.	What are MEMS micro-switches? How do they work and what types of actuation are used? Give two advantages over conventional mechanical switches.	5 Marks	L3	C05
	c.	Explain how a piezoelectric actuator generates force and displacement. Compare piezoelectric actuation with thermal actuation in terms of response speed, displacement, and power usage.	5 Marks	L3	C05